





60V N-CHANNEL SELF PROTECTED ENHANCEMENT MODE INTELLIFET™ MOSFET

Product Summary

 $\begin{array}{lll} \bullet & \text{Continuos Drain Source Voltage} & 60V \\ \bullet & \text{On-State Resistance} & 500 \text{m}\Omega \\ \bullet & \text{Nominal Load Current } (V_{\text{IN}} = 5V) & 1.3A \\ \bullet & \text{Clamping Energy} & 90 \text{mJ} \\ \end{array}$

Description

The ZXMS6004FF is a self protected low side MOSFET with logic level input. It integrates over-temperature, over-current, over-voltage (active clamp) and ESD protected logic level functionality. The ZXMS6004FF is ideal as a general purpose switch driven from 3.3V or 5V microcontrollers in harsh environments where standard MOSFETs are not rugged enough.

Applications

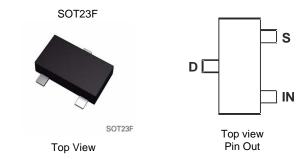
- Especially suited for loads with a high in-rush current such as lamps and motors
- All types of resistive, inductive and capacitive loads in switching applications
- μC compatible power switch for 12V and 24V DC applications
- Automotive rated
- · Replaces electromechanical relays and discrete circuits
- Linear Mode capability the current-limiting protection circuitry is
 designed to de-activate at low VDS to minimize on state power
 dissipation. The maximum DC operating current is therefore
 determined by the thermal capability of the package/board
 combination, rather than by the protection circuitry. This does not
 compromise the product's ability to self-protect at low VDS

Features and Benefits

- Compact High Power Dissipation Package
- Low Input Current
- Logic Level Input (3.3V and 5V)
- Short Circuit Protection with Auto Restart
- Over Voltage Protection (active clamp)
- Thermal Shutdown with Auto Restart
- Over-Current Protection
- Input Protection (ESD)
- High Continuous Current Rating
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable

Mechanical Data

- Case: SOT-23F
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish
- Weight: 0.012 grams (Approximate)



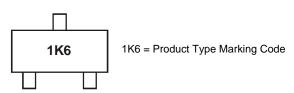
Ordering Information (Note 4)

Product	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
ZXMS6004FFQTA	1K6	7	12	3,000

Notes:

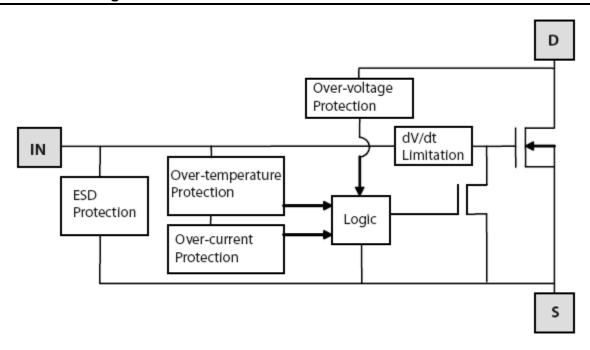
- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q10x and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_compliance_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information





Functional Block Diagram



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Continuous Drain-Source Voltage	V _{DS}	60	V
Drain-Source Voltage for Short Circuit Protection	V _{DS(SC)}	36	V
Continuous Input Voltage	V _{IN}	-0.5 +6	V
Continuous Input Current @-0.2V \leq V _{IN} \leq 6V Continuous Input Current @V _{IN} < -0.2V or V _{IN} > 6V	I _{IN}	No limit I _{IN} ≤2	mA
Pulsed Drain Current @V _{IN} = 3.3V	I _{DM}	2	A
Pulsed Drain Current @V _{IN} = 5V	I _{DM}	2.5	Α
Continuous Source Current (Body Diode) (Note 4)	I _S	1	Α
Pulsed Source Current (Body Diode)	I _{SM}	5	Α
Unclamped Single Pulse Inductive Energy, $T_J = +25^{\circ}C$, $I_D = 0.5A$, $V_{DD} = 24V$	E _{AS}	90	mJ
Electrostatic Discharge (Human Body Model)	V _{ESD}	4000	V
Charged Device Model	V _{CDM}	1000	V

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Power Dissipation at T _A = +25°C (Note 6) Linear Derating Factor	P _D	0.83 6.66	W mW/°C
Power Dissipation at T _A = +25°C (Note 7) Linear Derating Factor	P _D	1.5 12.0	W mW/°C
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	150	°C/W
Thermal Resistance, Junction to Ambient (Note 7)	R _{θJA}	83	°C/W
Thermal Resistance, Junction to Case (Note 8)	$R_{ heta JC}$	44	°C/W
Operating Temperature Range	TJ	-40 to +150	°C
Storage Temperature Range	T _{STG}	-55 to +150	°C

6. For a device surface mounted on 15mm x 15mm single sided, 1oz weight copper on 1.6mm FR4 board, in still air conditions. 7. For a device surface mounted on 50mm x 50mm single sided, 2oz weight copper on 1.6mm FR4 board, in still air conditions. Notes:

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^{8.} Thermal resistance from junction and the mounting surfaces of the drain pins.

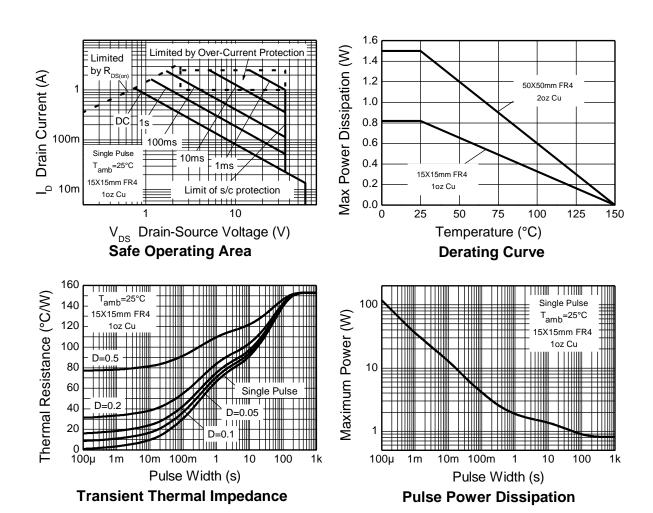


Recommended Operating Conditions

The ZXMS6004FF is optimized for use with μC operating from 3.3V and 5V supplies.

Characteristic	Symbol	Min	Max	Unit
Input Voltage Range	V _{IN}	0	5.5	V
Ambient Temperature Range	T _A	-40	+125	°C
High Level Input Voltage for MOSFET to be On	V _{IH}	3	5.5	V
Low Level Input Voltage for MOSFET to be Off	V_{IL}	0	0.7	V
Peripheral Supply Voltage (voltage to which load is referred)	V_{P}	0	36	V

Thermal Characteristics





Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Static Characteristics						
Drain-Source Clamp Voltage	V _{DS(AZ)}	60	65	70	V	$I_D = 10mA$
Off State Drain Current	1 .	_	_	500	nA	$V_{DS} = 12V, V_{IN} = 0V$
On State Drain Current	IDSS		_	1	μA	$V_{DS} = 36V, V_{IN} = 0V$
Input Threshold Voltage	V _{IN(th)}	0.7	1	1.5	V	$V_{DS} = V_{GS}$, $I_D = 1mA$
lanut Current		_	60	100	μA	V _{IN} = +3V
Input Current	I _{IN}	_	120	200		$V_{IN} = +5V$
Input Current While Over Temperature Active	_		_	220	μΑ	V _{IN} = +5V
Static Drain-Source On-State Resistance			400	600	mΩ	$V_{IN} = +3V, I_D = 0.5A$
Static Drain-Source On-State Resistance	R _{DS(on)}	_	350	500		$V_{IN} = +5V, I_D = 0.5A$
Continuous Drain Current (Note 6)	- I _D	0.9	_	_		V _{IN} = 3V; T _A = +25°C
Continuous Drain Current (Note 6)		1.0	_	_	А	$V_{IN} = 5V; T_A = +25^{\circ}C$
Continuous Drain Current (Note 7)		1.2	_	_		$V_{IN} = 3V; T_A = +25^{\circ}C$
Continuous Drain Current (Note 7)		1.3	_	_		$V_{IN} = 5V$; $T_A = +25$ °C
Current Limit (Note 9)	I _{D(LIM)}	0.7	1.7	_	Α	$V_{IN} = +3V$
Current Limit (Note 9)		1	2.2	_		$V_{IN} = +5V$
Dynamic Characteristics						
Turn On Delay Time	t _{d(on)}	1	5	_		
Rise Time	t _r	_	10	_		$V_{DD} = 12V$. $I_D = 0.5A$. $V_{GS} = 5V$
Turn Off Delay Time	t _{d(off)}	-	45	_	μs	$V_{DD} = 12V, I_D = 0.5A, V_{GS} = 5V$
Fall Time	f _f		15			
Over-Temperature Protection						
Thermal Overload Trip Temperature (Note 10)	T_{JT}	+150	+175	_	°C	
Thermal Hysteresis (Note 10)	f _f		+10		°C	_

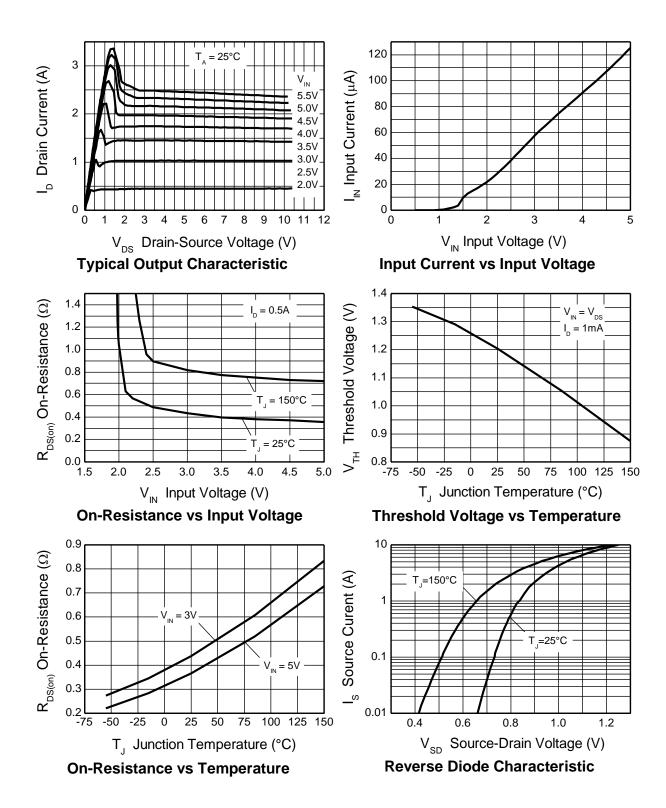
Notes:

^{9.} The drain current is restricted only when the device is in saturation (see graph 'typical output characteristic'). This allows the device to be used in the fully on state without interference from the current limit. The device is fully protected at all drain currents, as the low power dissipation generated outside saturation makes current limit unnecessary.

^{10.} Over-temperature protection is designed to prevent device destruction under fault conditions. Fault conditions are considered as "outside" normal operating range, so this part is not designed to withstand over-temperature for extended periods..

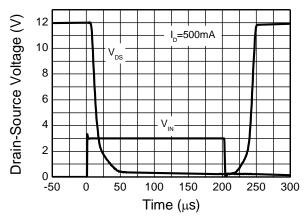


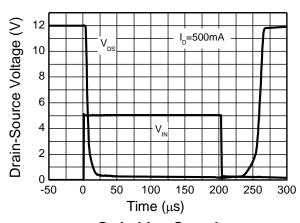
Typical Characteristics





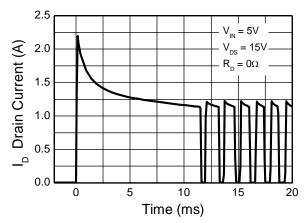
Typical Characteristics (cont.)





Switching Speed

Switching Speed

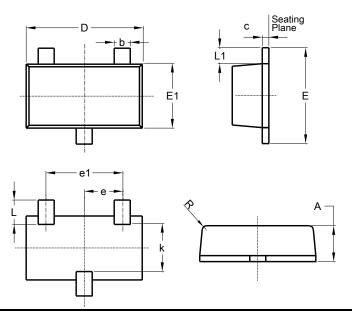


Typical Short Circuit Protection



Package Outline Dimensions

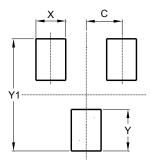
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT23F					
Dim	Min	Max	Тур		
Α	0.80	1.00	0.90		
b	0.35	0.45	0.40		
С	0.06	0.16	0.11		
D	2.80	3.00	2.90		
е	-	-	0.95		
e1	-	-	1.90		
Е	2.30	2.50	2.40		
E1	1.50	1.70	1.60		
k	1.10	1.26	1.18		
L	0.48	0.68	0.58		
L1	0.39	0.41	0.40		
R	0.05	0.15	0.10		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value		
Dilliensions	(in mm)		
C	0.95		
Х	0.80		
Y	1.110		
Y1	3.000		



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